Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Previously Presented) A method of manufacture of a semiconductor device, comprising the steps of:

providing an adhesive between a surface of a semiconductor chip having a plurality of electrodes on which said electrodes are provided and a surface of a substrate having a plurality of leads and an undivided film on which said leads and said undivided film are formed;

positioning at least one of said plurality of electrodes to be opposed to at least one of said plurality of leads such that said undivided film is opposed to said semiconductor chip; and

applying pressure in a direction such as to make a gap between said semiconductor chip and said substrate narrower such that said adhesive extends to be disposed on the whole of said undivided film;

wherein said undivided film is formed with a lower adhesion to said adhesive than a base material of said substrate, and said undivided film is broader than each of said leads at their portions opposed to said electrodes,

wherein a region on which said adhesive is disposed includes a first region with low adhesion to said adhesive and a second region with high adhesion to said adhesive,

an area of said first region $\geqq$ an area of said second region.

2. (Original) The method of manufacture of a semiconductor device as defined in claim 1,

wherein said adhesive is formed of an anisotropic conductive material having conductive particles dispersed in an insulating material.

3. (Previously Presented) The method of manufacture of a semiconductor device as defined in claim 1,

wherein said leads and said undivided film are formed by etching a conductive foil adhered to said base material of said substrate.

4. (Previously Presented) The method of manufacture of a semiconductor device as defined in claim 1,

wherein a conductive foil used when forming said leads is also used to form said undivided film.

5. (Previously Presented) The method of manufacture of a semiconductor device as defined in claim 4,

wherein said undivided film is formed simultaneously with said leads.

6. (Previously Presented) The method of manufacture of a semiconductor device as defined in claim 1,

wherein said electrodes are provided on an extremity of said surface of said semiconductor chip; and

wherein said undivided film is formed in a region opposing a central part of said surface of said semiconductor chip.

7. (Previously Presented) The method of manufacture of a semiconductor device as defined in claim 1,

wherein said undivided film is formed to spread two-dimensionally, with at least one opening exposing a surface of said substrate.

8. (Previously Presented) The method of manufacture of a semiconductor device as defined in claim 1,

wherein said undivided film is formed to project outside a region in which said semiconductor chip is adhered.

9. (Previously Presented) The method of manufacture of a semiconductor device as defined in claim 1,

wherein said undivided film is formed to be symmetrical about a center point of a region in which said semiconductor chip is adhered.

10. (Previously Presented) The method of manufacture of a semiconductor device as defined in claim 1,

wherein said undivided film is formed to avoid at least one of said leads.

11. (Canceled)

12. (Previously Presented) A semiconductor device comprising:

a semiconductor chip having a plurality of electrodes;

a substrate on which is formed a plurality of leads and an undivided film, said undivided film opposed to said semiconductor chip; and

an adhesive provided between a surface of said semiconductor chip on which said electrodes are formed and a surface of said substrate on which said leads and said undivided film are formed to adhere said semiconductor chip and said substrate, said adhesive disposed on the whole of said undivided film,

wherein at least one of said plurality of electrodes and at least one of said plurality of leads are electrically connected; and

wherein said undivided film is formed with a lower adhesion to said adhesive than a base material of said substrate, and said undivided film is broader than each of said leads at their portions opposed to said electrodes,

wherein a region on which said adhesive is disposed includes a first region with low adhesion to said adhesive and a second region with high adhesion to said adhesive,

an area of said first region $\geqq$ an area of said second region.

13. (Original) The semiconductor device as defined in claim 12,

wherein said adhesive is formed of an anisotropic conductive material having conductive particles dispersed in an insulating material.

14. (Previously Presented) The semiconductor device as defined in claim 12,

wherein said leads and said undivided film are formed of the same electrically conductive material.

15. (Previously Presented) The semiconductor device as defined in claim 12,

wherein said electrodes are provided at an extremity of said surface of said semiconductor chip; and

wherein said undivided film is formed in a region opposing a central part of said surface of said semiconductor chip.

16. (Previously Presented) The semiconductor device as defined in claim 12,

wherein said undivided film is formed to spread two-dimensionally, with at least one opening exposing a surface of said substrate.

17. (Previously Presented) The semiconductor device as defined in claim 12,

wherein said undivided film is formed to project outside a region in which said semiconductor chip is adhered.

18. (Previously Presented) The semiconductor device as defined in claim 12,

wherein said undivided film is formed to be symmetrical about a center point of a region in which said semiconductor chip is adhered.

19. (Previously Presented) The semiconductor device as defined in claim 12,

wherein said undivided film is formed to avoid at least one of said leads.

20. (Canceled)

21. (Original) A circuit board on which is mounted the semiconductor device as defined in claim 12.

22. (Original) An electronic instrument having the semiconductor device as defined in claim 12.

23-24. (Canceled).